



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{SSS}	R _{SS(ON) Max}	I _S T _A = +25°C
12V	$2.75 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	24.4A
	6.1mΩ @ V _{GS} = 2.5V	16.4A

Features

- CSP with Footprint 3.05mm x 1.77mm
- Height = 0.11mm for Low Profile
- · ESD Protection of Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{SS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

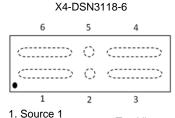
Mechanical Data

- Case: X4-DSN3118-6
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu. Solderable per MIL-STD-202, Method 208 @4)

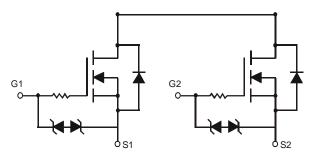
Applications

- Battery Management
- Load Switch
- Battery Protection





- 2. Gate 1 Top View
- 3. Source 1
- 4. Source 2
- 5. Gate 2
- 6. Source 2



Equivalent Circuit

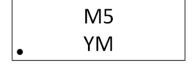
Ordering Information (Note 4)

Ī	Part Number	Case	Packaging
	DMN1002UCA6-7	X4-DSN3118-6	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\begin{array}{l} M5 = Product\ Type\ Marking\ Code \\ YM = Date\ Code\ Marking \\ Y\ or\ \overline{Y} = Year\ (ex:\ F = 2018) \\ M\ or\ \overline{M} = Month\ (ex:\ 9 = September) \end{array}$

Date Code Kev

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Year	2017	2018	20	019	2020	2021		20)22	2023	202	24	2025
Code	E	F		G	Н			,	J	K	L	5	M
Month	Jan	Feb	Mar	Apr	May	Jun	Jι	ıl	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	·	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Source-Source Voltage	Vsss	12	V		
Gate-Source Voltage	V_{GSS}	±8	V		
Continuous Source Current (Note 5) V _{GS} = 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	Is	24.4 19.6	Α
Continuous Source Current (Note 5) V _{GS} = 2.5V	Is	16.4 13.1	А		
Pulsed Source Current (Note 6)	I _{SM}	100	Α		

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	P _D	1.10	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 7)	$R_{\theta JA}$	114.1	°C/W
Power Dissipation (Note 5)	P _D	2.47	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	$R_{\theta JA}$	50.7	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

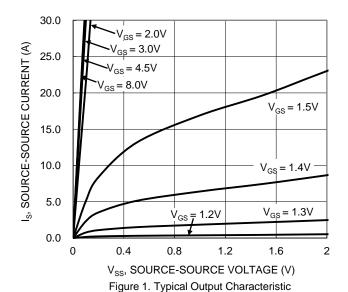
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Source-Source Breakdown Voltage	BV _{SSS}	12	_	_	V	$V_{GS} = 0V$, $I_S = 1mA$
Zero Gate Voltage Drain Current T _J = +25°C	I _{SSS}	_	_	1	μA	$V_{SS} = 9.6V, V_{GS} = 0V$
Coto Source Leekage		_	_	±10	μΑ	$V_{GS} = \pm 8V, V_{SS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±1.0	μΑ	$V_{GS} = \pm 5V$, $V_{SS} = 0V$
ON CHARACTERISTICS (Note 8)						•
Gate Threshold Voltage	V _{GS(TH)}	0.35	0.8	1.4	V	Vss = 10V, Is = 1.41mA
		1.5	2.27	2.75		$V_{GS} = 4.5V, I_S = 6A$
Static Source Source On Booletones	R _{SS(ON)}	1.6	2.36	2.85	mΩ	$V_{GS} = 3.8V, I_S = 6A$
Static Source-Source On-Resistance		1.7	2.54	3.95		$V_{GS} = 3.1V, I_S = 6A$
		1.9	2.9	6.1		$V_{GS} = 2.5V, I_S = 6A$
Diode Forward Voltage	Vss	_	0.69	1.2	V	$V_{GS} = 0V, I_{S} = 6A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	_	3062	4593		10/1/
Output Capacitance	Coss	_	758	1137	pF	$V_{SS} = 10V, V_{GS} = 0V,$ f = 1kHz
Reverse Transfer Capacitance	C _{rss}	_	198	297		I = INIIZ
Total Gate Charge	Qg	_	45.7	68.6		
Gate-Source Charge	Q _{gs}	_	8.3	12.5	nC	$V_{SS} = 8V$, $V_{GS} = 4V$,
Gate-Drain Charge	Q _{gd}	_	16.0	24.0	IIC	$I_S = 6A$
Gate Charge at V _{TH}	$Q_{g(th)}$	_	4.5	6.8		
Turn-On Delay Time	t _{D(ON)}	_	1005	1508		
Turn-On Rise Time	t _R	_	2186	3279		$V_{SS} = 8V$, $V_{GS} = 4V$,
Turn-Off Delay Time	t _{D(OFF)}	_	2643	3965	ns	I _S = 6A
Turn-Off Fall Time	t _F	_	4193	6290		

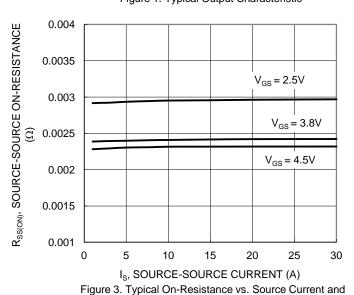
Notes:

- 5. Device mounted on FR-4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.
 6. Repetitive rating, pulse width limited by junction temperature.
 7. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to production testing.









Gate Voltage

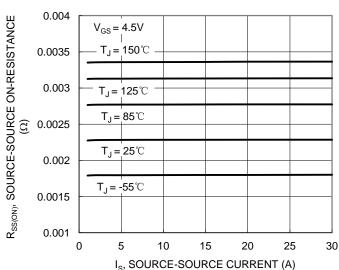
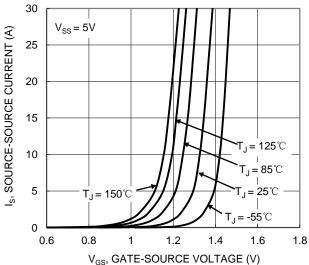
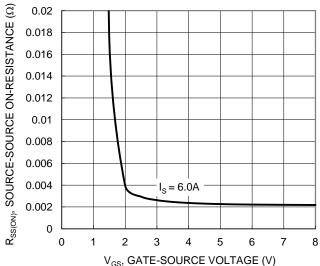


Figure 5. Typical On-Resistance vs. Source Current and Junction Temperature



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic

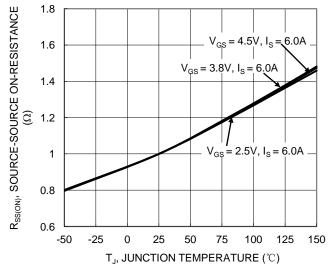


Figure 6. On-Resistance Variation with Junction Temperature



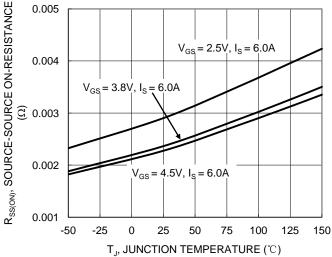
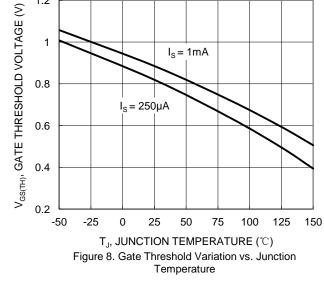


Figure 7. On-Resistance Variation with Junction Temperature



1.2

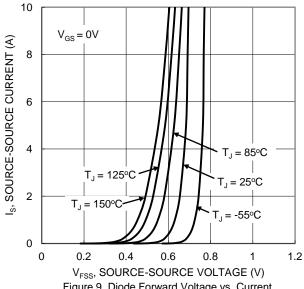
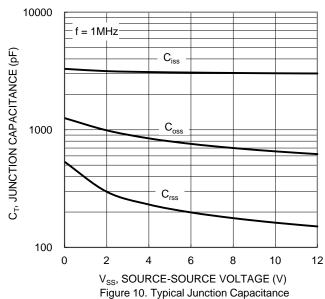
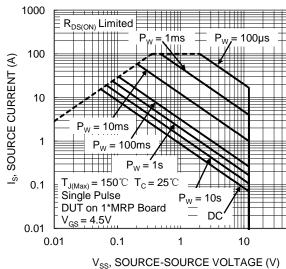


Figure 9. Diode Forward Voltage vs. Current





8 7 6 5 4 3 $V_{SS} = 8.0V, I_{S} = 6.0A$ 2 0 10 20 30 40 50 60 70 80 90 Q_q (nC)

Figure 11. Gate Charge Figure 12. SOA, Safe Operation Area

100



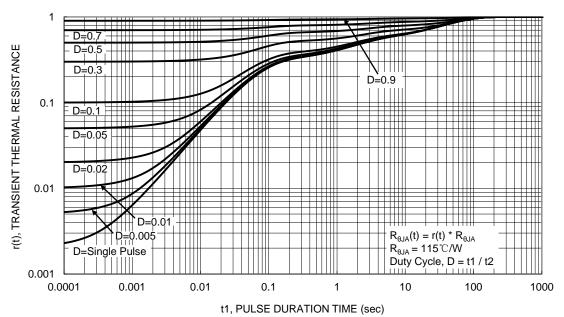


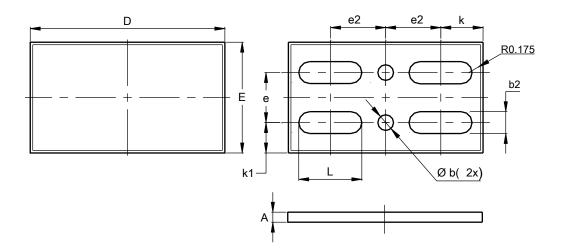
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X4-DSN3118-6

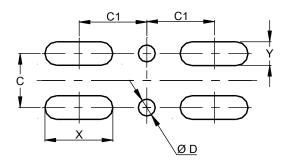


X4-DSN3118-6							
Dim	Min	Max	Тур				
Α	0.09	0.16	0.11				
b			0.25				
b2	0.32	0.38	0.35				
D	3.00	3.10	3.05				
Е	1.72	1.82	1.77				
е			0.800				
e2			0.878				
k			0.648				
k1			0.485				
L	0.975	1.035	1.005				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X4-DSN3118-6



Dimensions	Value (in mm)			
С	0.800			
C1	0.878			
D	0.250			
Х	1.005			
Y	0.350			



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